Diode Semiconductor Device - Page 1 of 1



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Inclosure Mat	eria:
Metal	
Overall Lengt	h:
0.570 inches	
Terminal Leng	gth:
Between 1.000) inches and 1.625 inches
Overall Diame	eter:
Between 0.215	5 inches and 0.235 inches
Function For	Which Designed:
Transient supp	pressor
Joint Electror	ic Device Engineering Council/jedec/case Outline Designation:
Do-13	
Electrode Inte	rnally-electrically Connected To Case:
Cathode	
Mounting Met	hod:
Terminal	
Semiconducto	or Material:
Silicon	
Voltage Ratin	g In Volts Per Characteristic:
171.0 working	peak reverse voltage
Current Ratin	g Per Characteristic:
200.00 ampere	es forward current, average preset
Power Rating	Per Characteristic:
1.0 watts smal	l-signal input power, common-collector horsepower metric
Maximum Ope	erating Tempurature Per Measurement Point:
175.0 degrees	celsius junction
Test Data Doo	sument:
81349-mil-s-19	500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; exclud	les commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental	and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Terminal Type	e And Quantity:
2 uninsulated v	wire lead
Specification	Data:
81349-mil-s-19	0500/500 government specification
Shelf Life:	
N/a	
Unit Of Measu	ire:
Demilitarizatio	on:
No	
Fiig:	
A110a0	